

Claims

1. (Previously presented) A microelectronic device comprising:
a die, the die comprising a first side, a second side, and an edge;
a first plate, the first plate coupled with the die, the first plate exerting force on the die to modify the effective coefficient of thermal expansion of the die; and
a package, the die being coupled with the package.
2. (Cancelled)
3. (Previously presented) The microelectronic device of claim 1, where the first plate modifies the coefficient of thermal expansion of the die to make the coefficient of thermal expansion of die more closely match the coefficient of thermal expansion of the package.
4. (Currently amended) The microelectronic device of claim 1, wherein the first plate comprises a hole, the die fitting within the hole, the edge of the die being coupled with an edge of the first plate by the hole.
5. (Original) The microelectronic device of claim 4, wherein the edge of the die is soldered with the edge of the first plate.
6. (Original) The microelectronic device of claim 1, wherein a side of the die is coupled with a side of the first plate.
7. (Original) The microelectronic device of claim 1, further comprising a second plate coupled with the package.

8. (Original) The microelectronic device of claim 7, wherein the package is attached with the second plate by an adhesive.
9. (Original) The microelectronic device of claim 7, wherein the first plate and second plate are constructed of the same material.
10. (Original) The microelectronic device of claim 9, wherein the first plate and the second plate are constructed of copper.
- 11-30. (Cancelled)
31. (Currently amended) A microelectronic device comprising:
a die, the die comprising a first side, a second side, and an edge;
a first plate, the first plate coupled with the die, the first plate comprising a hole,
the die fitting within the hole, the edge of the die being coupled with an
edge of the first plate by the hole, the edge of the die being soldered with
the edge of the first plate; and
a package, the die being coupled with the package.
32. (Previously presented) The microelectronic device of claim 31, wherein the first plate exerts forces on the die to modify its effective coefficient of thermal expansion.
33. (Previously presented) The microelectronic device of claim 32, where the first plate modifies the coefficient of thermal expansion of the die to make the coefficient of thermal expansion of die more closely match the coefficient of thermal expansion of the package.

34. (Previously presented) The microelectronic device of claim 31, further comprising a second plate coupled with the package.
35. (Previously presented) The microelectronic device of claim 34, wherein the package is attached with the second plate by an adhesive.
36. (Previously presented) The microelectronic device of claim 35, wherein the first plate and second plate are constructed of the same material.
37. (Previously presented) The microelectronic device of claim 36, wherein the first plate and the second plate are constructed of copper.